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SPC-F005.DWG

REVISIONS

DOC. NO. SPC-F005 • Effective: 7/8/02 • DCP No: 1398

DCP #	REV	DESCRIPTION	DRAWN	DATE	CHECKD	DATE	APPRVD	DATE
1885	A	RELEASED	EO	02/03/06	HO	2/6/06	JWM	2/6/06



Description: Silicon TO-126, PNP Power Transistor for use in power amplifier and switching excellent safe area limits.

Absolute Maximum Ratings:

- Collector-Base Voltage, $V_{CB0} = 80V$
- Collector-Emitter Voltage, $V_{CE0} = 80V$
- Emitter-Base Voltage, $V_{EB0} = 5V$
- Continuous Collector Current, $I_C = 4A$
- Base Current = 1A
- Total Device Dissipation ($T_C = +25^\circ C$), $P_D = 40W$
Derate above $25^\circ C = 320mW/^\circ C$
- Operating Junction Temperature Range, $T_J = -65^\circ$ to $+150^\circ C$
- Storage Temperature Range, $T_{stg} = -65^\circ$ to $+150^\circ C$

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Max	Unit
OFF Characteristics					
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100mA, I_B = 0, (Note 1)$	80	-	V
Collector Cut-Off Current	I_{CBO}	$V_{CE} = 80V, I_E = 0$	-	1	mA
Collector Cut-Off Current	I_{CEX}	$V_{CE} = 80V, V_{EB(off)} = 1.5V$	-	0.1	mA
	I_{CBO}	$V_{CB} = 80V, I_E = 0$	-	0.1	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	-	1	mA

ON Characteristics

DC Current Gain (Note 1)	h_{FE}	$V_{CE} = 2V, I_C = 1.5A$	20	80	-
		$V_{CE} = 2V, I_C = 4A$	7	-	-
Collector-Emitter Saturation Voltage (Note 1)	$V_{CE(sat)}$	$I_C = 1.5A, I_B = .15mA$	-	0.6	V
		$I_C = 4A, I_B = 1A$	-	1.4	V
Base-Emitter On Voltage (Note 1)	$V_{BE(on)}$	$I_C = 1.5A, V_{CE} = 2V$	-	1.2	V

Small-Signal Characteristics

Current Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 1A, f = 1MHz$	2	-	MHz
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Note 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

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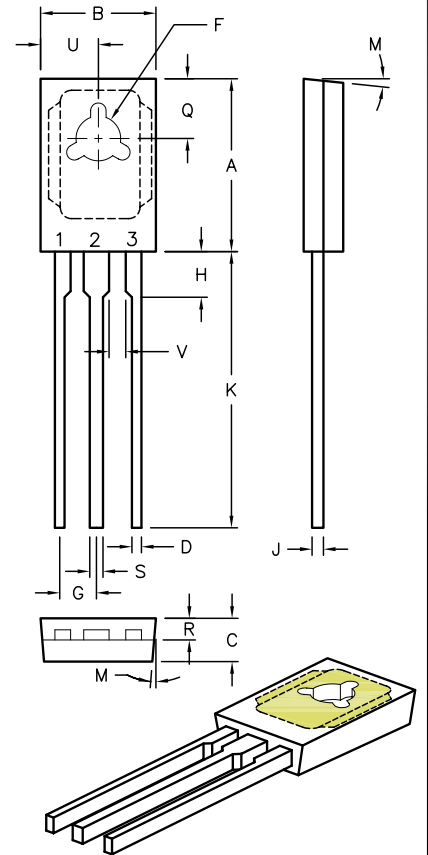
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DRAWING TITLE:			
Transistor, Bipolar, Plastic, TO-126, PNP			
SIZE	DWG. NO.	ELECTRONIC FILE	REV
A	2N5195	01H1379.DWG	A
SCALE:	NTS	U.O.M.: MILLIMETERS	SHEET: 1 OF 1

PNP

Dim	Min	Max
A	10.80	11.05
B	7.49	7.75
C	2.41	2.67
D	0.51	0.66
F	2.92	3.18
G	2.31	2.46
H	1.27	2.41
J	0.38	0.64
K	15.11	16.64
M	3' TYP	
Q	3.76	4.01
R	1.14	1.40
S	0.64	0.89
U	3.68	3.94
V	1.02	-



STYLE 1

- PIN 1. EMITTER
- 2. COLLECTOR
- 3. BASE

3 COLLECTOR

